

L Number	Hits	Search Text	DB	Time stamp
4	19036	(SAC (self near5 align\$3 near5 contact))	USPAT; US-PGPUB	2004/06/11 23:59
5	5071	((SAC (self near5 align\$3 near5 contact))) and gate	USPAT; US-PGPUB	2004/06/11 23:59
6	4914	((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove)	USPAT; US-PGPUB	2004/06/11 23:59
7	4508	((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove) and (etch\$3 pattern\$3)	USPAT; US-PGPUB	2004/06/11 20:30
8	3723	((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove) and (etch\$3 pattern\$3)) and (polysilicon (polycrystal\$6 near3 silicon) a-Si a-silicon (alpha near3 silicon) (alpha-silicon alpha-si))	USPAT; US-PGPUB	2004/06/11 23:59
9	4389	((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove) and (etch\$3 pattern\$3)) and (polysilicon (polycrystal\$6 near3 silicon) a-Si a-silicon (alpha near3 silicon) (alpha-silicon alpha-si) metal conduct\$3)	USPAT; US-PGPUB	2004/06/11 20:31
11	1592	((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove) and (etch\$3 pattern\$3)) and (polysilicon (polycrystal\$6 near3 silicon) a-Si a-silicon (alpha near3 silicon) (alpha-silicon alpha-si) metal conduct\$3)) and (bit-line (bit near3 line) bit?line)	USPAT; US-PGPUB	2004/06/12 00:00
12	4556	(SAC (self near5 align\$3 near5 contact))	EPO; JPO; DERWENT; IBM_TDB	2004/06/11 23:59
13	1170	((SAC (self near5 align\$3 near5 contact))) and gate	EPO; JPO; DERWENT; IBM_TDB	2004/06/11 23:59
14	1147	((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove)	EPO; JPO; DERWENT; IBM_TDB	2004/06/11 23:59
15	410	((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove) and (polysilicon (polycrystal\$6 near3 silicon) a-Si a-silicon (alpha near3 silicon) (alpha-silicon alpha-si))	EPO; JPO; DERWENT; IBM_TDB	2004/06/12 00:00
16	141	((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove) and (bit-line (bit near3 line) bit?line)	EPO; JPO; DERWENT; IBM_TDB	2004/06/12 00:00
17	51	((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove) and (polysilicon (polycrystal\$6 near3 silicon) a-Si a-silicon (alpha near3 silicon) (alpha-silicon alpha-si)) and (((SAC (self near5 align\$3 near5 contact))) and gate) and (via hole trench recess contact groove) and (bit-line (bit near3 line) bit?line))	EPO; JPO; DERWENT; IBM_TDB	2004/06/12 00:00